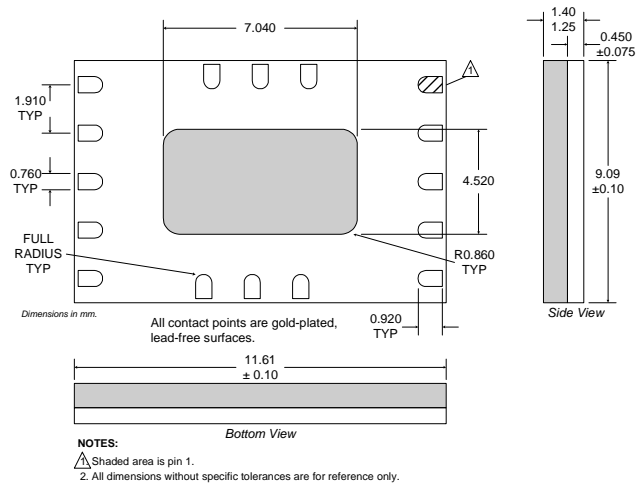


Typical Applications

- 3V Dual-Band GSM/DCS Handsets
- Commercial and Consumer Systems
- Portable Battery-Powered Equipment
- GPRS Compatible
- GSM, E-GSM and DCS Products

Product Description

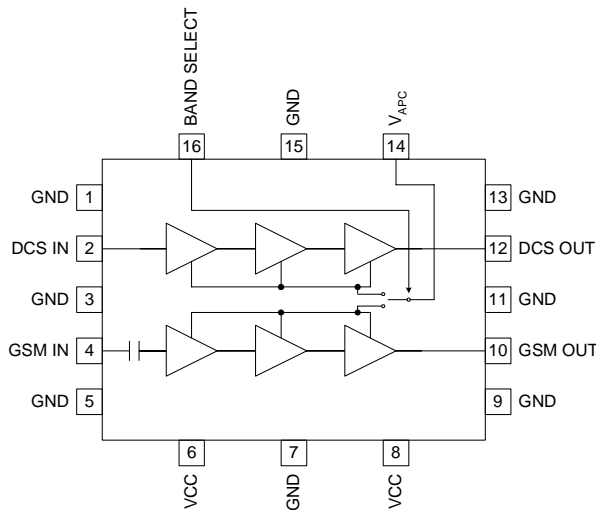
The RF3160 is a high-power, high-efficiency power amplifier module. The device is self-contained with 50Ω input and output terminals. The device is manufactured on an advanced Gallium Arsenide Heterojunction Bipolar Transistor (HBT) process, and has been designed for use as the final RF amplifier in GSM/DCS handheld digital cellular equipment and other applications in the 880MHz to 915MHz and 1710MHz to 1785MHz bands. On-board power control provides over 70dB of control range with an analog voltage input, and provides power down with a logic "low" for standby operation. The device is packaged in an ultra-small (9mmx11mm) LCC, minimizing the required board space.



Optimum Technology Matching® Applied

- Si BJT       GaAs HBT       GaAs MESFET  
 Si Bi-CMOS       SiGe HBT       Si CMOS

Package Style: Module (9mmx11mm)



Functional Block Diagram

Features

- Single 2.8V to 5.0V Supply Voltage
- +35.0dBm GSM Output Power at 3.2V
- +32.5dBm DCS Output Power at 3.2V
- 55% GSM and 50% DCS Efficiency
- Internal Band Select

Ordering Information

- RF3160      Dual-Band GSM/DCS Power Amp Module  
 RF3160 PCBA      Fully Assembled Evaluation Board

RF Micro Devices, Inc.  
7625 Thorndike Road  
Greensboro, NC 27409, USA

Tel (336) 664 1233  
Fax (336) 664 0454  
<http://www.rfmd.com>

## Absolute Maximum Ratings

Parameter	Rating	Unit
Supply Voltage	-0.5 to +5.0	V <sub>DC</sub>
Power Control Voltage (V <sub>APC1,2</sub> )	-0.5 to +3.0	V
DC Supply Current	2400	mA
Input RF Power	+15	dBm
Duty Cycle at Max Power	50	%
Output Load VSWR	6:1	
Operating Case Temperature	-30 to +85	°C
Storage Temperature	-30 to +85	°C



**Caution!** ESD sensitive device.

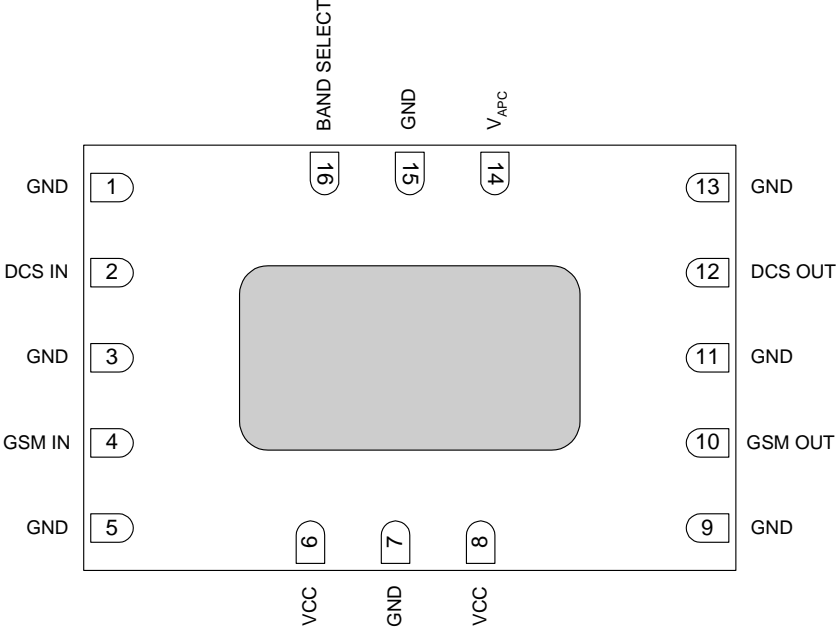
RF Micro Devices believes the furnished information is correct and accurate at the time of this printing. However, RF Micro Devices reserves the right to make changes to its products without notice. RF Micro Devices does not assume responsibility for the use of the described product(s).

Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>Overall (GSM Mode)</b>					Temp=+25°C, V <sub>CC</sub> =3.2V, V <sub>APCGSM</sub> =1.9V, P <sub>IN</sub> =6dBm, Freq=880MHz to 915MHz, 25% Duty Cycle, Pulse Width=1154µs
Operating Frequency Range		880 to 915		MHz	
Maximum Output Power	34.5	35.0		dBm	Temp = 25°C, V <sub>CC</sub> =3.2V, V <sub>APCGSM</sub> =1.9V
PAE Efficiency	50	55		%	At P <sub>OUT·MAX</sub> , V <sub>CC</sub> =3.2V
Input Power for Max Output	+6	+8	+10	dBm	
Output Noise Power			-72	dBm	RBW=100kHz, 925MHz to 935MHz, P <sub>OUT</sub> ≥34.5dBm
			-84	dBm	RBW=100kHz, 935MHz to 960MHz, P <sub>OUT</sub> ≥34.5dBm
Forward Isolation			-40	dBm	V <sub>APCGSM</sub> =0.1V, P <sub>IN</sub> =-5dBm
Cross-Band Isolation			-15	dBm	P <sub>OUT</sub> ≥34.5dBm
Second Harmonic			-7	dBm	5dBm < P <sub>OUT</sub> ≤ 34.5dBm
Third Harmonic			-7	dBm	
All Other Non-Harmonic Spurious			-7	dBm	
Input Impedance		50		Ω	
Input VSWR			3:1		
Output Load VSWR (Stability)	6:1				Spurious < -36dBm, V <sub>APCGSM</sub> =0.1V to 1.9V, RBW=3MHz
Output Load VSWR (Ruggedness)	10:1				P <sub>IN</sub> =6dBm, P <sub>OUT</sub> ≤34.5dBm, V <sub>CC</sub> =4.6V, Z <sub>S</sub> =50Ω
Output Load Impedance		50		Ω	Load impedance presented at RF OUT pad
<b>Power Control V<sub>APC1</sub></b>					
Power Control "ON"	1.8		1.9	V	Max. P <sub>OUT</sub>
Power Control "OFF"	0.1	0.5		V	Min. P <sub>OUT</sub>
Power Control Range	60			dB	V <sub>APC1,2</sub> =0.1V to 1.9V
Gain Control Slope		100		dB/V	P <sub>OUT</sub> =-10dBm to 34.5dBm
APC Input Capacitance			10	pF	DC to 2MHz
APC Input Current			1	mA	V <sub>APC</sub> =1.9V
			10	µA	V <sub>APC</sub> =0V
Turn On/Off Time			2	µS	V <sub>APC</sub> =0V to 1.9V
Band Select	0		0.5	V	GSM
	2		2.8	V	DCS
<b>Overall Power Supply</b>					
Power Supply Voltage	2.8	3.2	5.0	V	Specifications
	2.9		4.7	V	Nominal operating limits, P <sub>OUT</sub> ≤+34.5dBm
Power Supply Current		2		A	DC Current at P <sub>OUT·MAX</sub>
			30	µA	V <sub>APC1,2</sub> =0.1V. No RF input power.

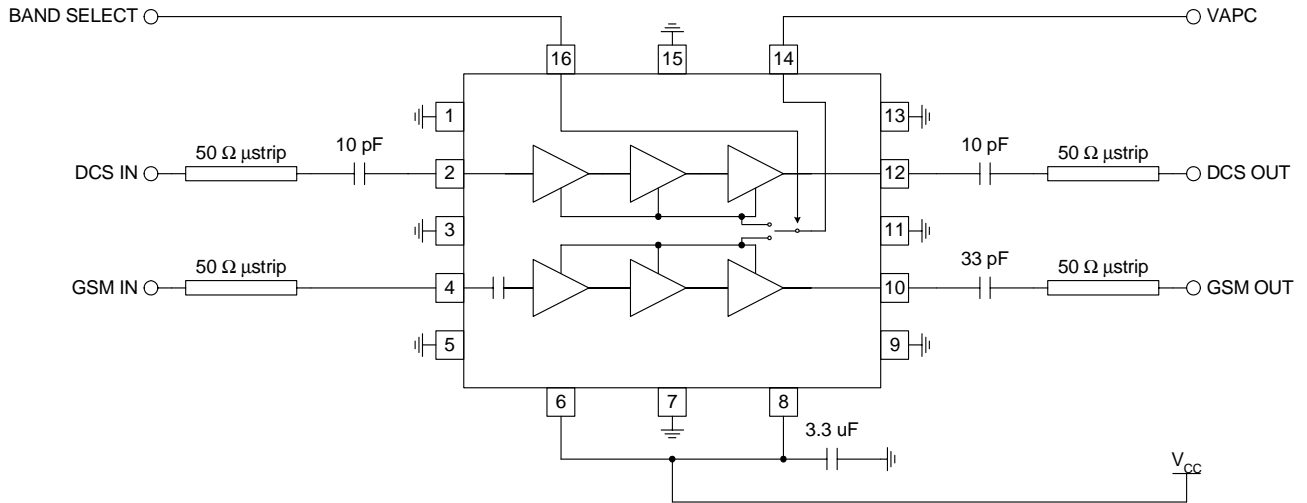
Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>Overall (DCS Mode)</b>					Temp=25°C, V <sub>CC</sub> =3.2V, V <sub>APCDCS</sub> =1.9V, P <sub>IN</sub> =6dBm, Freq=1710MHz to 1785MHz, 25% Duty Cycle, pulse width=1154μs
Operating Frequency Range		1710 to 1785		MHz	
Maximum Output Power	31.9	32.5		dBm	Temp=25°C, V <sub>CC</sub> =3.2V, V <sub>APCDCS</sub> =1.9V, 1710MHz to 1785MHz
PAE Efficiency	42	50		%	At P <sub>OUT,MAX</sub> , V <sub>CC</sub> =3.2V, 1710MHz to 1785MHz
Recommended Input Power Range	+6	+8	+10	dBm	
Output Noise Power		-80	-76	dBm	RBW=100kHz, 1805MHz to 1880MHz, P <sub>OUT</sub> ≥ 32.5dBm, V <sub>CC</sub> =3.2V
Forward Isolation			-48	dBm	V <sub>APCDCS</sub> =0.1V, P <sub>IN</sub> =-5dBm
Second Harmonic			-7	dBm	0dBm < P <sub>OUT</sub> ≤ 32.5dBm
Third Harmonic			-7	dBm	
All Other Non-Harmonic Spurious			-7	dBm	
Input Impedance		50		Ω	
Input VSWR			3:1		
Output Load VSWR (Stability)	6:1				Spurious < -36dBm, V <sub>APCDCS</sub> =0.1V to 1.9V, RBW=3MHz
Output Load VSWR (Ruggedness)	10:1				P <sub>IN</sub> =6dBm, P <sub>OUT</sub> ≤ 31.9dBm, V <sub>CC</sub> =4.6V, Z <sub>S</sub> =50Ω
Output Load Impedance		50		Ω	Load impedance presented at RF OUT pin
<b>Power Control V<sub>APC2</sub></b>					
Power Control "ON"	1.8		1.9	V	Max. P <sub>OUT</sub>
Power Control "OFF"	0.1	0.5		V	Min. P <sub>OUT</sub>
Power Control Range	60			dB	V <sub>APC1,2</sub> =0.1V to 1.9V
Gain Control Slope		100		dB/V	P <sub>OUT</sub> =-10dBm to +32.5dBm
APC Input Capacitance			10	pF	DC to 2MHz
APC Input Current			1	mA	V <sub>APC</sub> =1.9V
			10	μA	V <sub>APC</sub> =0V
Turn On/Off Time			100	ns	V <sub>APC</sub> =0 to 1.9V
<b>Overall Power Supply</b>					
Power Supply Voltage	2.9	3.2	4.7	V	Specifications
				V	Nominal operating limits, P <sub>OUT</sub> ≤ +32.5dBm
Power Supply Current		1.3		A	DC Current at P <sub>OUT,MAX</sub>
			30	μA	V <sub>APC1,2</sub> =0.1V. No RF input power.

Pin	Function	Description	Interface Schematic
1	<b>GND</b>	Connects to module backside ground.	
2	<b>DCS IN</b>	RF input to the DCS band. This is a 50Ω input, external DC-blocking capacitor required. See application schematic.	
3	<b>GND</b>	Connects to module backside ground.	
4	<b>GSM IN</b>	RF input to the GSM band. This is a 50Ω input. No external DC-blocking capacitor required. See application schematic.	
5	<b>GND</b>	Connects to module backside ground.	
6	<b>VCC</b>	Power supply for stages 1 and 2 of both the GSM and DCS power amplifiers. External low frequency bypassing capacitor required. See application schematic.	
7	<b>GND</b>	Connects to module backside ground.	
8	<b>VCC</b>	Power supply for output stages of both the GSM and DCS power amplifiers. External low frequency bypassing capacitor required. See application schematic.	
9	<b>GND</b>	Connects to module backside ground.	
10	<b>GSM OUT</b>	RF output for the GSM band. This is a 50Ω output. External DC-blocking capacitor required. See application schematic.	
11	<b>GND</b>	Connects to module backside ground.	
12	<b>DCS OUT</b>	RF output for the DCS band. This is a 50Ω output. External DC-blocking capacitor required. See application schematic.	
13	<b>GND</b>	Connects to module backside ground.	
14	<b>VAPC</b>	Single input analog power control voltage for the GSM and DCS band.	
15	<b>GND</b>	Connects to module backside ground.	
16	<b>BAND SELECT</b>	Logic low (GSM enable) or logic high (DCS enable) provides single IO band selection.	
<b>Pkg Base</b>	<b>GND</b>	Module backside ground.	

Pin Out  
Top View



## Application Schematic

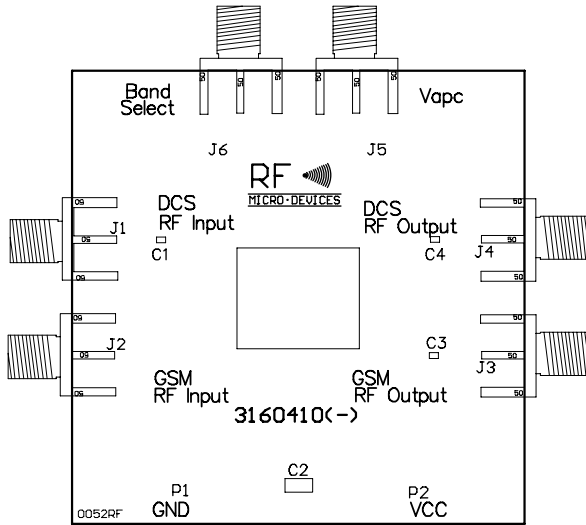


### Evaluation Board Layout Board Size 2.0" x 2.0"

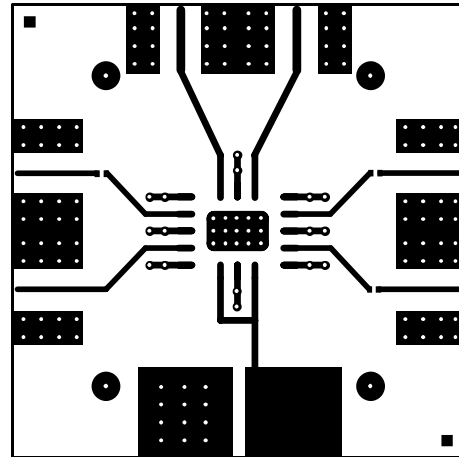
Board Thickness 0.032", Board Material FR-4, Multi-Layer

Assembly

Top



Inner 1



Back

